
2SJ218

Silicon P-Channel MOS FET

HITACHI

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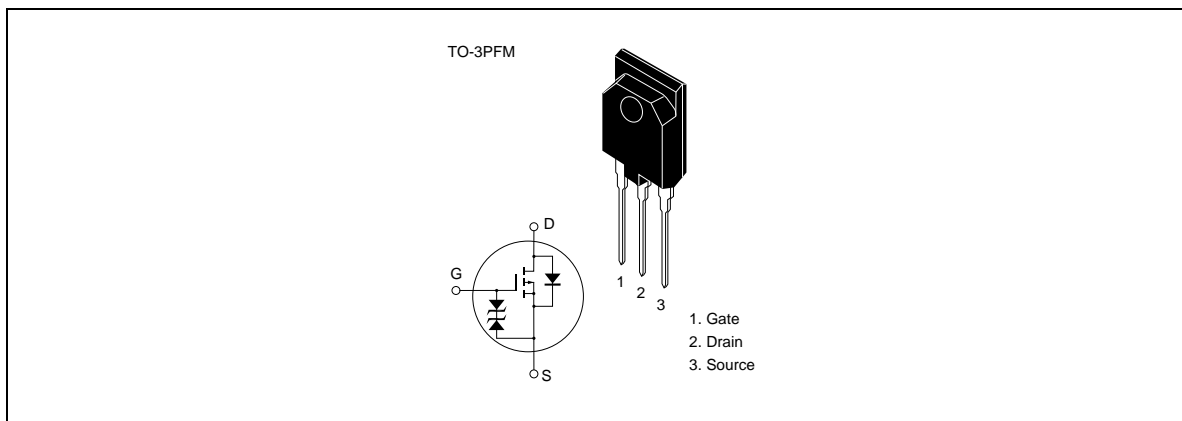
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	−60	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	−45	A
Drain peak current	$I_{D(pulse)}^{*1}$	−180	A
Body to drain diode reverse drain current	I_{DR}	−45	A
Channel dissipation	Pch^{*2}	60	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

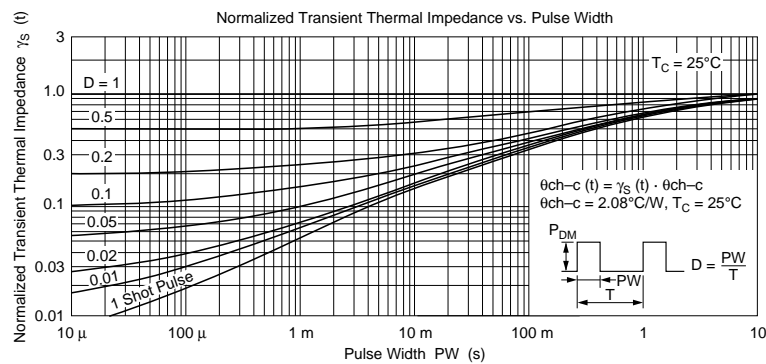
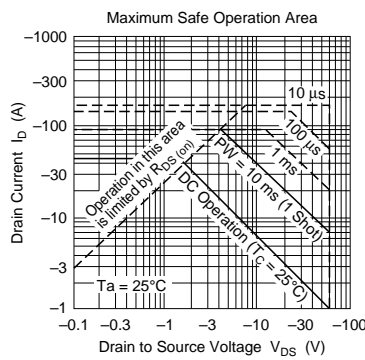
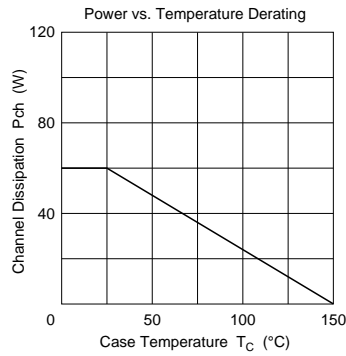
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-250	μA	$V_{DS} = -50 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.033	0.042	Ω	$I_D = -20 \text{ A}$, $V_{GS} = -10 \text{ V}^{*1}$
		—	0.045	0.06		$I_D = -20 \text{ A}$, $V_{GS} = -4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	16	25	—	S	$I_D = -20 \text{ A}$, $V_{DS} = -10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	3800	—	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	2000	—	pF	
Reverse transfer capacitance	C_{rss}	—	490	—	pF	
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = -20 \text{ A}$, $V_{GS} = -10 \text{ V}$, $R_L = 1.5 \text{ }\Omega$
Rise time	t_r	—	235	—	ns	
Turn-off delay time	$t_{d(off)}$	—	670	—	ns	
Fall time	t_f	—	450	—	ns	
Body to drain diode forward voltage	V_{DF}	—	-1.35	—	V	$I_F = -45 \text{ A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = -45 \text{ A}$, $V_{GS} = 0$, $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SJ217



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